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Title: METHOD OF FORMING A GATE ELECTRODE, METHOD OF MANUFACTURING A SEMICONDUCTOR DEVICE HAVING THE GATE ELECTRODE, AND METHOD OF OXIDIZING A SUBSTRATE

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U.S. PATENT DOCUMENTS

<u>Exam Init</u>	<u>Ref</u>	<u>Document Number</u>	<u>Issue Date</u>	<u>Name</u>	<u>Class</u>	<u>Sub Class</u>
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FOREIGN PATENT DOCUMENTS

<u>Exam Init</u>	<u>Ref</u>	<u>Document Number</u>	<u>Publication Date</u>	<u>Country</u>	<u>Name</u>
_____	_____	JP8032066	2/2/1996	Japan	Katsuichi
_____	_____	JP11345970	12/14/1999	Japan	Tomio et al.

OTHER DOCUMENTS

<u>Exam Init</u>	<u>Ref</u>	<u>Author, Title, Date, Pertinent Pages, Etc.)</u>
_____	_____	English language of Abstract for Japanese Patent Publication No. JP8032066, filed 2/2/1996.
_____	_____	English language of Abstract for Japanese Patent Publication No. JP11345970, filed 12/14/1999.

Examiner: _____

Date Considered: _____